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	Filing Date		2006-06-16	
	First Named Inventor	Levent Gulari		
	Art Unit	TBA		
	Examiner Name	TBA		
Attorney Docket Number		FIS920030182US1		

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1	Haver H B et al. "Three-Dimensional Silicon on Oxide Device Isolation" Motorola Technical Developments, Motorola Inc. Schaumburg, Illinois, US vol. 7, 1 October 1987 (1987-10-1) pages 20-21, XP000050047	<input type="checkbox"/>
2	Mao B-Y et al. "The Effect of Post-Oxygen-Implant Annealing Temperature on the Channel Mobilities of CMOS Devices in Oxygen-Implanted Silicon-On-Insulator Structures" IEEE Electron Device Letters, IEEE Service Center, New York, NY US vol. EDL-8, no. 7 July 1987 (1987-07), pages 306-308, XP000821840	<input type="checkbox"/>

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